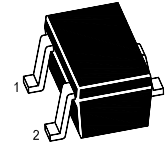


NPN Silicon Epitaxial Planar Transistor

for switching and amplifier applications



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	40	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	200	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 1\text{ V}$, $I_C = 0.1\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 1\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 10\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 50\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 100\text{ mA}$	h_{FE} h_{FE} h_{FE} h_{FE} h_{FE}	40 70 100 60 30	- - 300 - -	- - - - -
Collector Emitter Cutoff Current at $V_{CE} = 30\text{ V}$	I_{CES}	-	50	nA
Emitter Base Cutoff Current at $V_{EB} = 3\text{ V}$	I_{EBO}	-	50	nA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	60	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	40	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$ at $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	$V_{CE(sat)}$	- -	0.2 0.3	V
Base Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$ at $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	$V_{BE(sat)}$	0.65 -	0.85 0.95	V
Transition Frequency at $V_{CE} = 20\text{ V}$, $-I_E = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	300	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 100\text{ KHz}$	C_{ob}	-	4	pF
Delay Time at $V_{CC} = 3\text{ V}$, $V_{BE(OFF)} = 0.5\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = 1\text{ mA}$	t_d	-	35	ns
Rise Time at $V_{CC} = 3\text{ V}$, $V_{BE(OFF)} = 0.5\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = 1\text{ mA}$	t_r	-	35	ns
Storage Time at $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = -I_{B2} = 1\text{ mA}$	t_{stg}	-	200	ns
Fall Time at $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = -I_{B2} = 1\text{ mA}$	t_f	-	50	ns

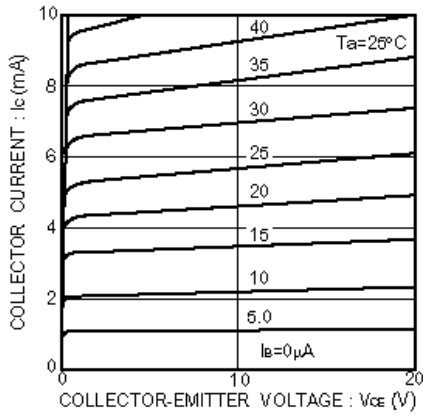


Fig.1 Grounded emitter output characteristics

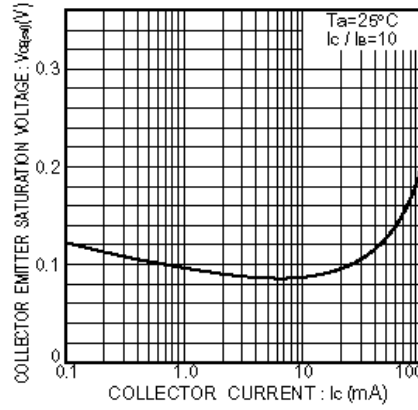


Fig.2 Collector-emitter saturation voltage vs. collector current

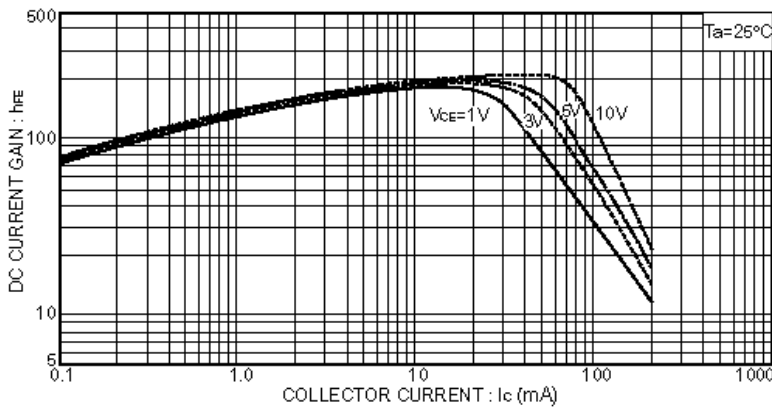


Fig.3 DC current gain vs. collector current (I)

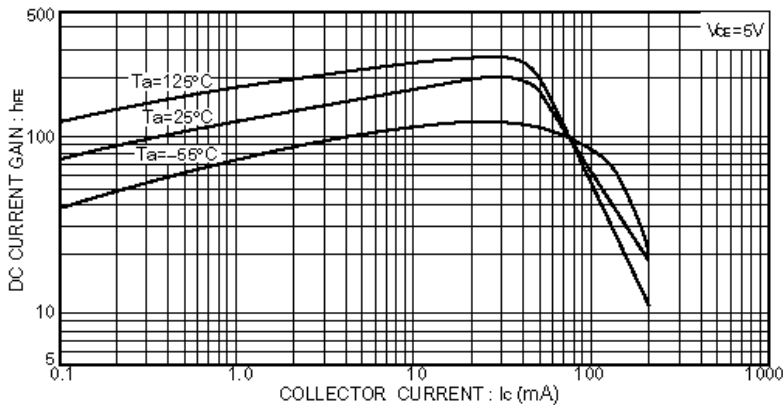


Fig.4 DC current gain vs. collector current (II)

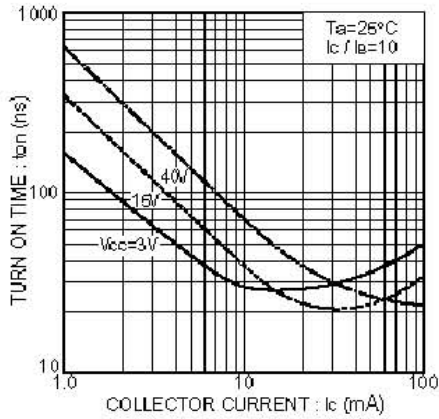


Fig.5 Turn-on time vs. collector current

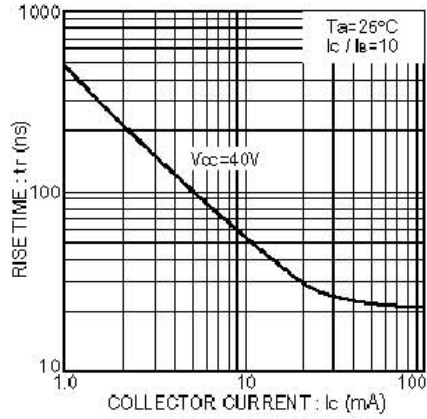


Fig.6 Rise time vs. collector current

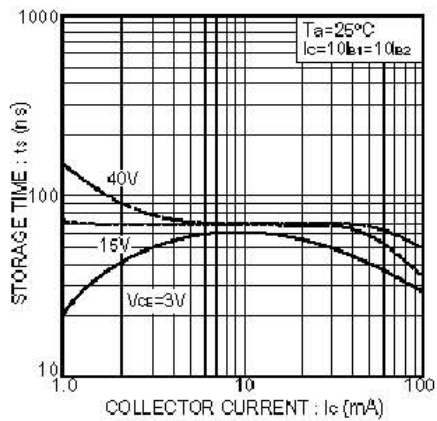


Fig.7 Storage time vs. collector current

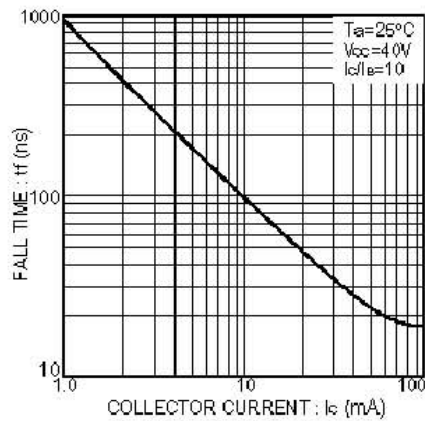


Fig.8 Fall time vs. collector current

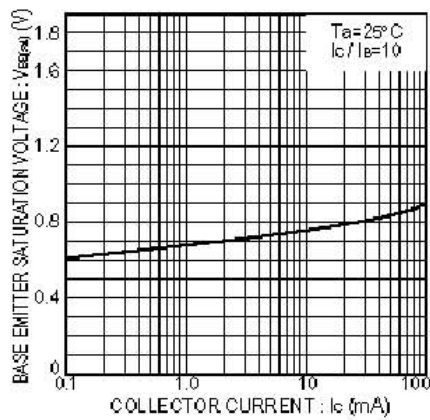


Fig.9 Base-emitter saturation voltage vs. collector current

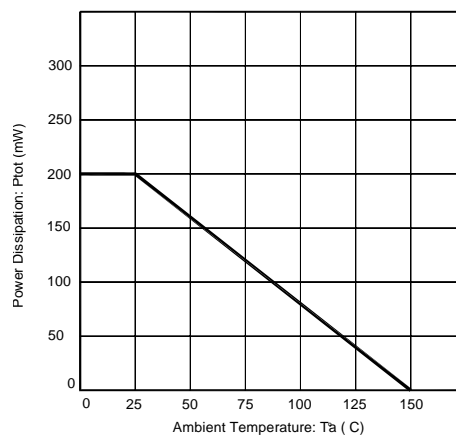
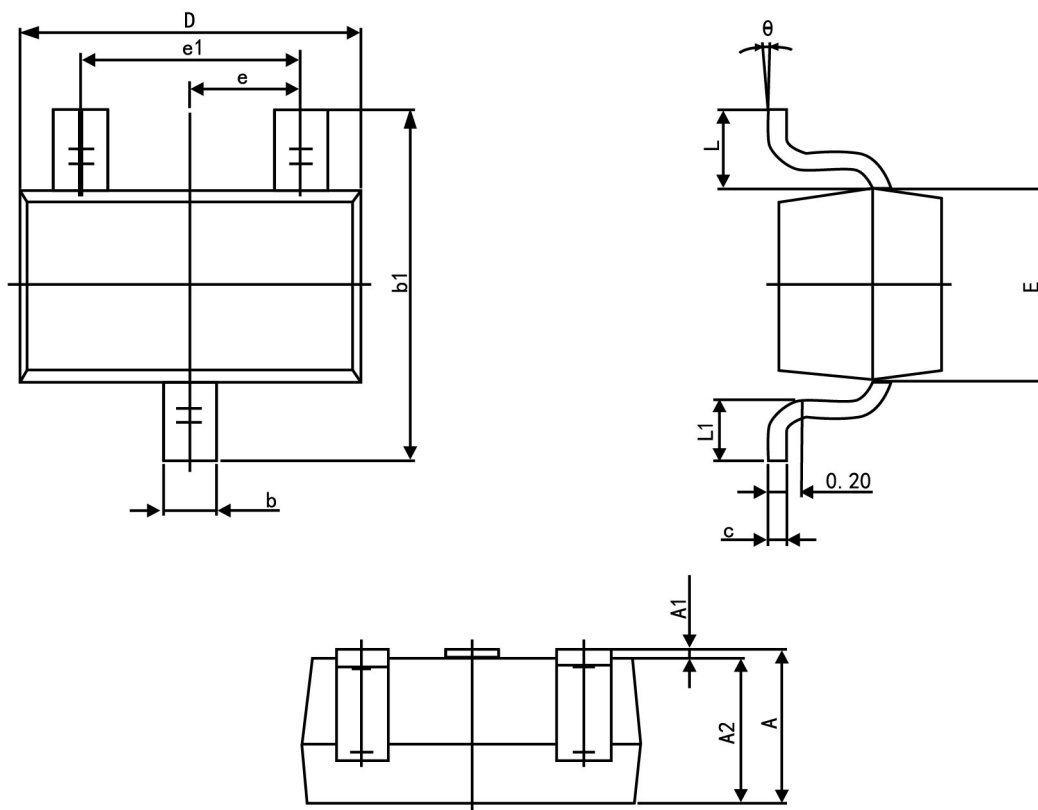


Fig.10 Power Dissipation vs Ambient Temperature

SOT-323 Package Outline Dimensions


Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.200	0.400
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
theta	0°	8°